
FOREWORD

Special Section on Fundamentals and Applications of Advanced Semiconductor Devices

This special section contains about 27 papers, which cover the fields of MOSFET technology, Emerging technology, III-V semiconductor technology, Nanoscale device technology Memory technology and Circuit technology. Recent years, innovations of electronic devices are strongly required for the various electronics fields such as information processing, communications, sensor electronics and power electronics and so on. The purpose of this special section is to discuss the progress of the new device technologies for the innovations from the fundamental physics to the processing technologies.

I would like to express my thanks to all authors for their contributions to the special section. I also thank all reviewers and editorial committee members for their devoted contributions to reviewing and editing the papers. Without their efforts, this special section couldn't be achieved.

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Tetsu Kachi, Guest Editor

Tetsu Kachi (*Member*) received the B.E., M.E. and Ph.D. degrees in applied physics from Nagoya University in 1975, 1977 and 1985, respectively. He joined Toyota Central R&D Labs. Inc. in 1978. His researches in the laboratory were optical measuring system, GaAs laser, GaN laser and GaN LED developments. Since 2000, his main interest has been GaN power devices. He received IR100 award in 1984 and JJAP paper award in 2008. He served as chair of the Electron Devices (ED) Technical Committee of IEICE from 2011 to 2012. He is now a Fellow of Toyota Central R&D Labs. Inc.

